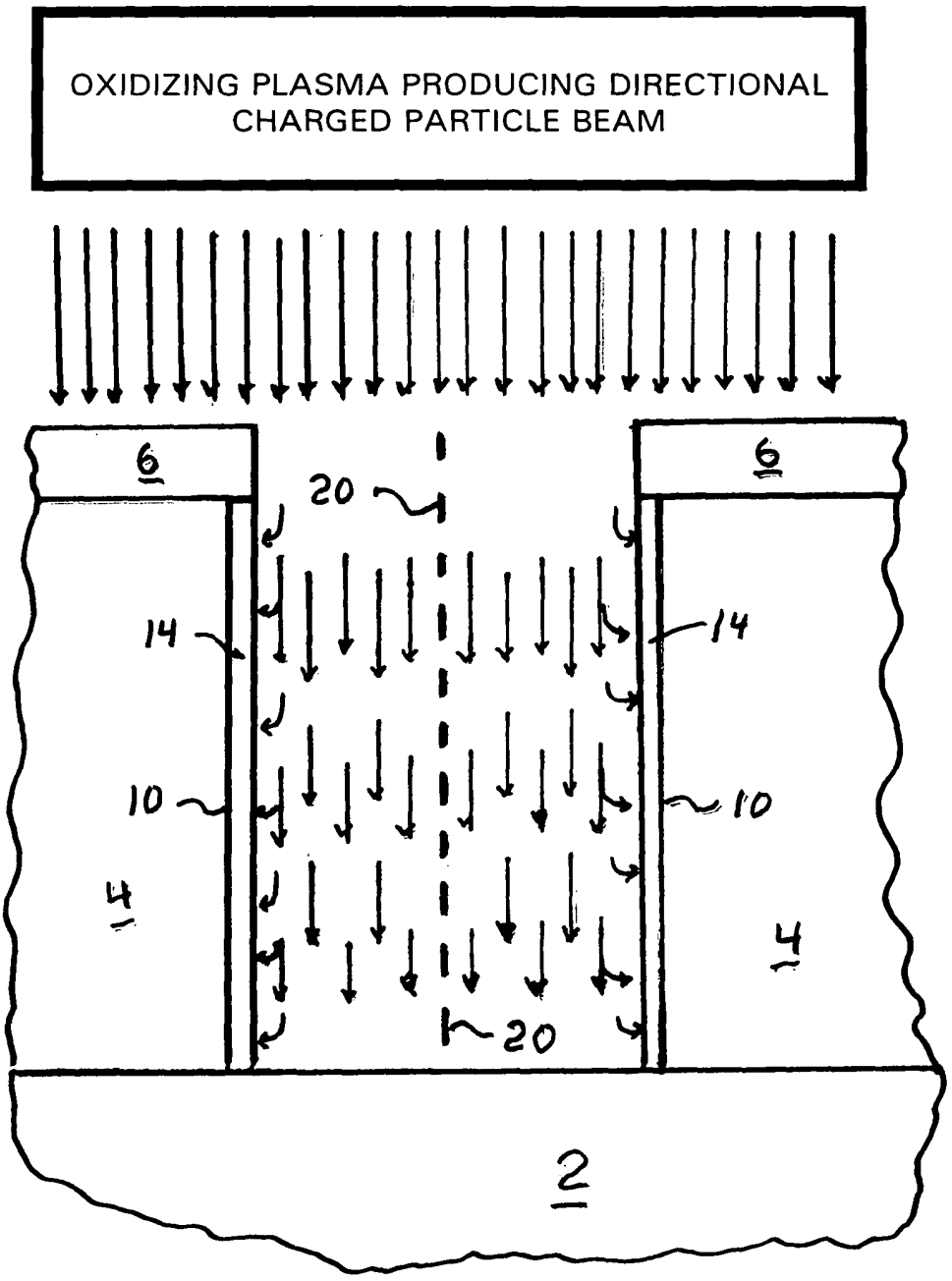
OXIDIZING PLASMA PRODUCING DIRECTIONAL CHARGED PARTICLE BEAM
6
6
20
14
14
10
10
4
4
20
2

FIGURE 1

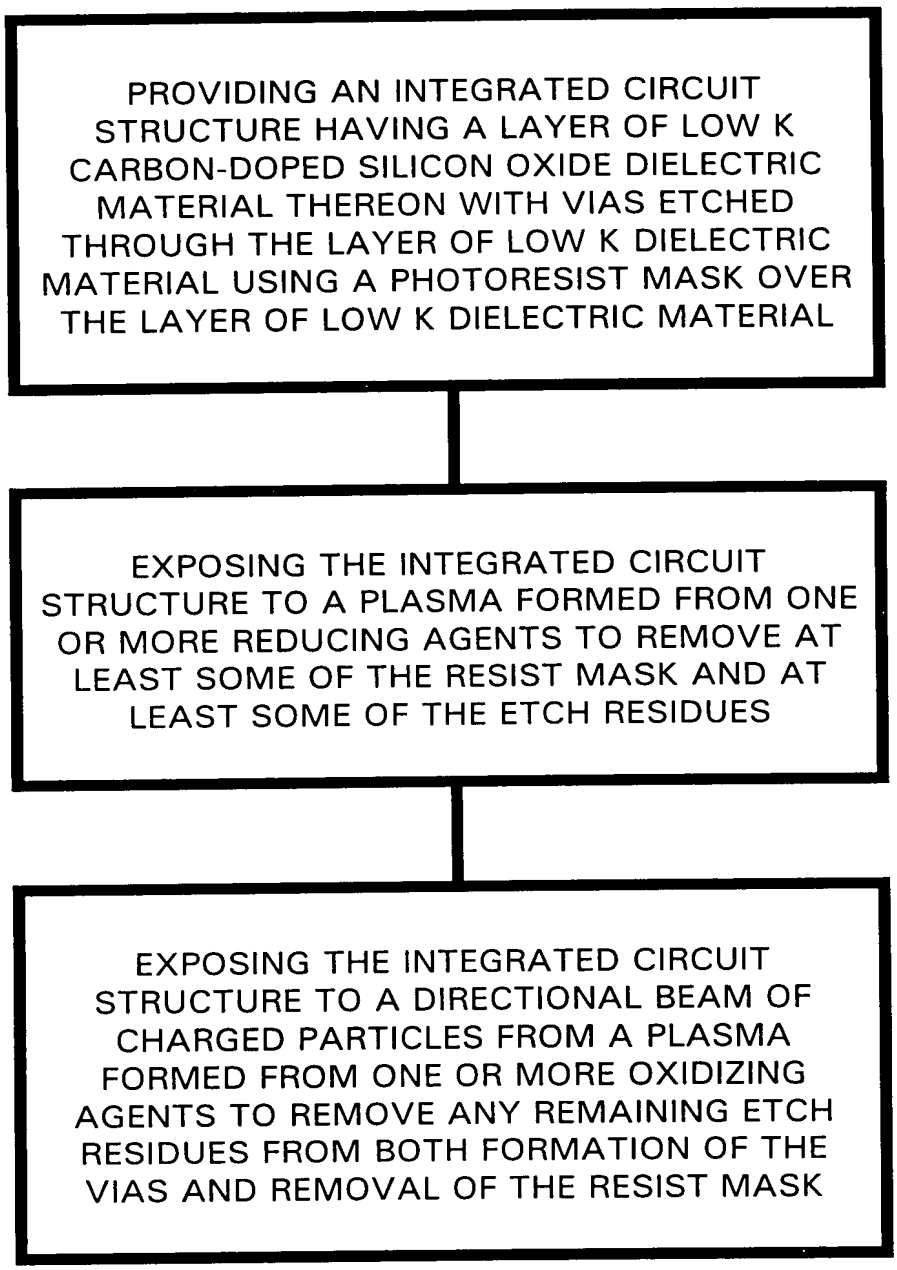
PROVIDING AN INTEGRATED CIRCUIT STRUCTURE HAVING A LAYER OF LOW K CARBON-DOPED SILICON OXIDE DIELECTRIC MATERIAL THEREON WITH VIAS ETCHED THROUGH THE LAYER OF LOW K DIELECTRIC MATERIAL USING A PHOTORESIST MASK OVER THE LAYER OF LOW K DIELECTRIC MATERIAL
EXPOSING THE INTEGRATED CIRCUIT STRUCTURE TO A PLASMA FORMED FROM ONE OR MORE REDUCING AGENTS TO REMOVE AT LEAST SOME OF THE RESIST MASK AND AT LEAST SOME OF THE ETCH RESIDUES
EXPOSING THE INTEGRATED CIRCUIT STRUCTURE TO A DIRECTIONAL BEAM OF CHARGED PARTICLES FROM A PLASMA FORMED FROM ONE OR MORE OXIDIZING AGENTS TO REMOVE ANY REMAINING ETCH RESIDUES FROM BOTH FORMATION OF THE VIAS AND REMOVAL OF THE RESIST MASK

FIGURE 2